

36- 40GHz Integrated Down Converter

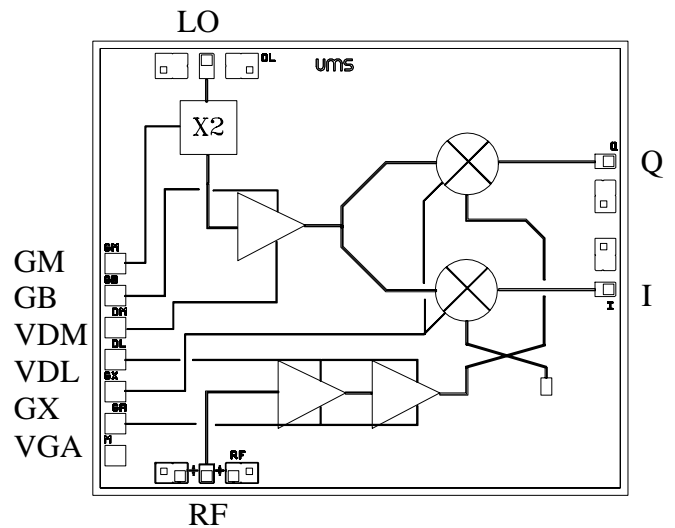
GaAs Monolithic Microwave IC

preliminary

Description

The CHR2296 is a multifunction chip which integrates a LO time two multiplier, a balanced cold FET mixer, and a RF LNA. It is designed for a wide range of applications, typically commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

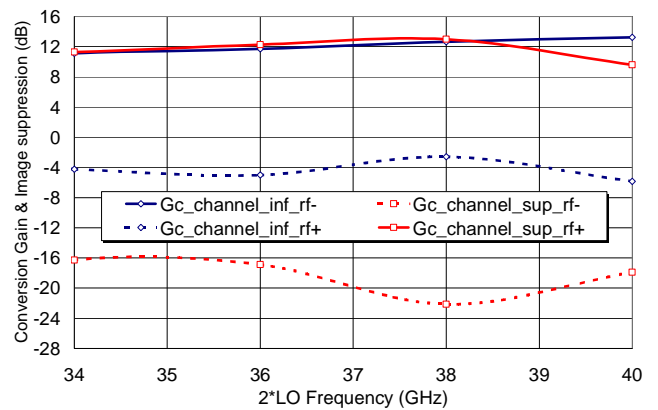
The circuit is manufactured with a PM-HEMT process, 0.25 μ m gate length, via holes through the substrate, air bridges and electron beam gate lithography. It is available in chip form.



Main Features

- Broadband performances : 36-40GHz
- 11 dB conversion gain
- 5dB noise figure
- 10dBm LO input power
- -10dBm RF input power (1dB gain comp.)
- Low DC power consumption, 110mA@3.5V
- Chip size : 2.49 X 1.97 X 0.10 mm

Typical on wafer measurement:



Conversion Gain & Image suppression @ IF=1GHz

Main Characteristics

Tamb. = 25°C

	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	36		40	GHz
F _{LO}	LO frequency range	17		20	GHz
F _{IF}	IF frequency range	0.25		1.5	GHz
G _c	Conversion gain		11		dB

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Ref. : DSCHR22962147 25-May-02

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Specifications subject to change without notice

Electrical Characteristics for Broadband Operation

T_{amb} = +25°C, V_d = 3.5V*preliminary*

Symbol	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	36		40	GHz
F _{LO}	LO frequency range	17		20	GHz
F _{IF}	IF frequency range	0.25		1.5	GHz
G _c	Conversion gain (1)		11		dB
NF	Noise Figure (1)		5		dB
P _{LO}	LO Input power		+10		dBm
Img Sup	Image Suppression		15		dBc
P1dB	Input power at 1dB gain compression		-10		dBm
LO VSWR	Input LO VSWR (1)		2.0:1		
RF VSWR	Input RF VSWR (1)		3.0:1		
I _d	Bias current (2)		110		mA

(1) On Wafer measurements

(2) Current source biasing network is recommended. Optimum performances for I_{dm}= 50mA and I_{dl}= 60mA

Absolute Maximum Ratings

T_{amb.} = 25°C (1)

Symbol	Parameter	Values	Unit
V _d	Maximum drain bias voltage	4.0	V
I _d	Maximum drain bias current	200	mA
V _g	Gate bias voltage	-2.0 to +0.4	V
V _{gd}	Minimum negative gate drain voltage (V _g – V _d)	-5	V
P _{in}	Maximum peak input power overdrive (2)	+15	dBm
T _{ch}	Maximum channel temperature	175	°C
T _a	Operating temperature range	-40 to +85	°C
T _{stg}	Storage temperature range	-55 to +125	°C

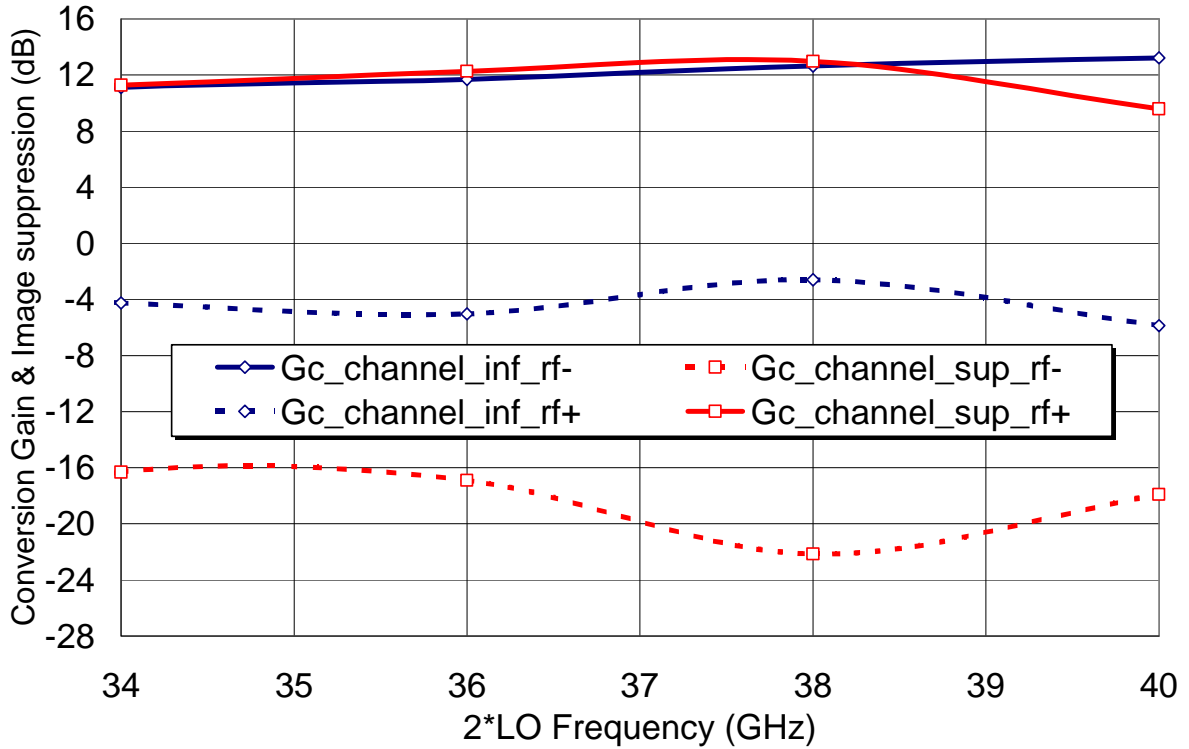
(1) Operation of this device above anyone of these parameters may cause permanent damage.

(2) Duration < 1s.

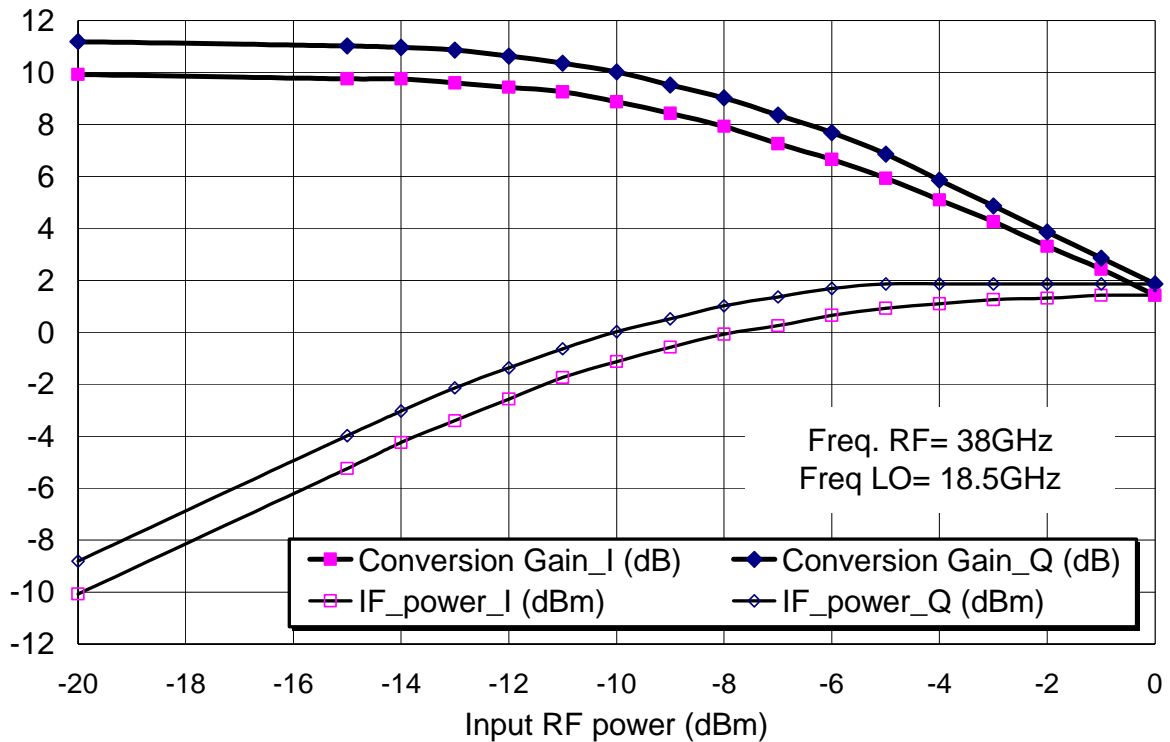
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Typical On-wafer Measurements

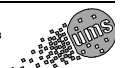
Bias Conditions : $V_{dm} = V_{dl} = 3.5\text{ V}$, $V_{gm} = -0.9\text{ V}$, $V_{gb} = -0.4\text{ V}$, $V_{gx} = -0.8\text{ V}$, $V_{ga} = -0.5\text{ V}$



Conversion gain & Image suppression with a 90° IQ combiner @ IF=1GHz

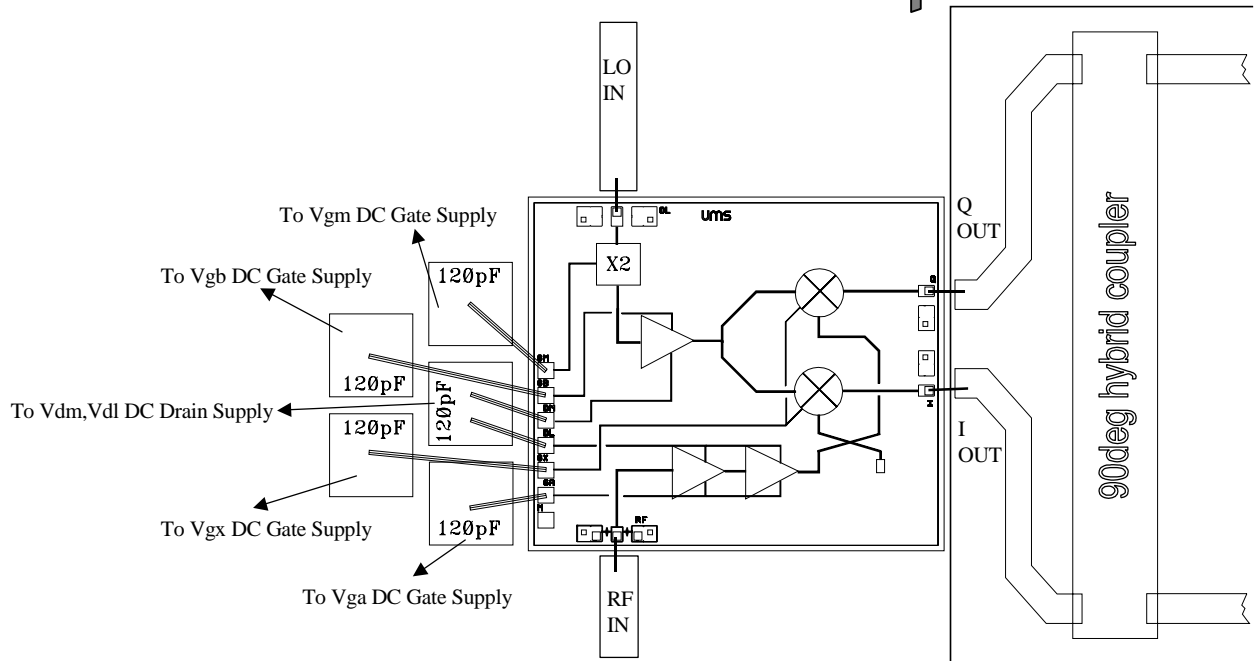


Input RF compression by channel

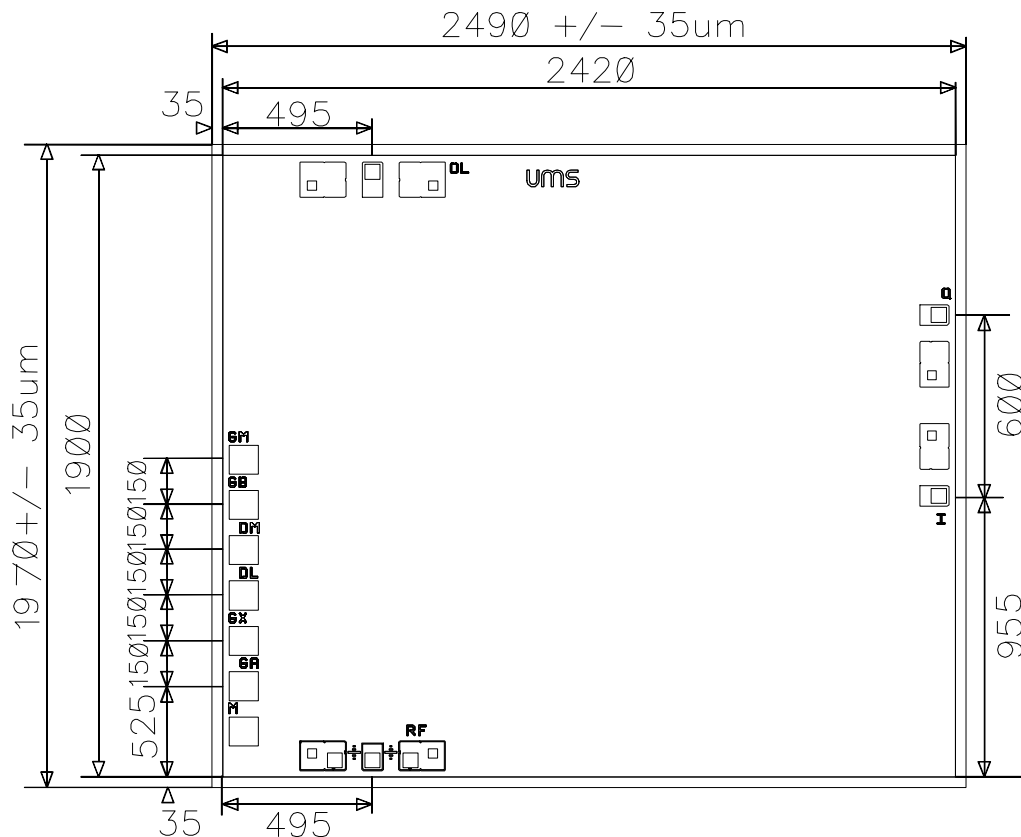


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Chip Assembly and Mechanical Data

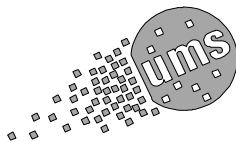


Note : Supply feed should be capacitively bypassed. 25µm diameter gold wire is recommended



Bonding pad positions

(Chip thickness : 100µm. All dimensions are in micrometers)



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Ordering Information

Chip form : CHR2296-99F/00

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